

**In the Claims:**

**Claim 1 (previously presented):** A flash memory device, comprising:

- a. a substrate;
- b. at least one core stack, wherein the at least one core stack comprises:
  - (1) a tunnel oxide layer on the substrate;
  - (2) a first polysilicon layer on the tunnel oxide layer;
  - (3) an anti-reflective interpoly layer atop and in contact with the first polysilicon layer, said anti-reflective interpoly layer having an index of refraction  $n$  and a thickness  $d$  and being configured for use with a light having a wavelength  $\lambda_1$ , such that  $d$  is an odd numbered multiple of approximately  $\lambda_1/4n$ ; and
  - (4) a transmissive second polysilicon layer on the anti-reflective interpoly layer;
- c. at least one source region adjacent to the at least one core stack; and
- d. at least one drain region adjacent to the at least one core stack.

**Claim 2 (previously presented):** The flash memory device, as recited in Claim 1, wherein the at least one source region and the at least one drain region are formed by the method comprising the steps of:

- a. depositing a layer of photoresist over the substrate and the at least one core stack;
- b. illuminating the layer of photoresist with said light;

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- c. transmitting some of the light through the transmissive second polysilicon layer;
- d. preventing the reflection of the light at the anti-reflective interpoly layer;
- e. removing part of the photoresist layer; and
- f. implanting a dopant into the substrate.

**Claim 3 (previously presented):** The flash memory device, as recited in Claim 2, wherein the light has an integer number  $m$  wavelengths incident upon the anti-reflective interpoly layer, and wherein

$$d \cong \frac{(m + \frac{1}{2})\lambda_i}{2n}, \text{ where } m = 0, 1, 2, \dots$$

**Claim 4 (previously presented):** The flash memory device, as recited in Claim 1, wherein  $d \cong \frac{\lambda_i}{4n}$ .

**Claim 5 (previously presented):** The flash memory device, as recited in Claim 1, wherein the anti-reflective interpoly layer is made of silicon oxynitride (SiON).

**Claim 6 (original):** The flash memory device, as recited in Claim 5, wherein the thickness of the anti-reflective interpoly layer is between about 300 to 400 Å thick.

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**Claim 7 (original):** The flash memory device, as recited in Claim 2, wherein the step of depositing the layer of photoresist, deposits the photoresist onto a surface of the transmissive second polysilicon layer.

**Claims 8-15 (canceled)**